



National Semiconductor™

Discrete POWER & Signal Technologies

Pro Electron Bipolar Devices

Device No.	Case Style	V _{CES} * V _{CEO} (V) Min	V _{CE0} (V) Min	V _{EB0} (V) Min	I _{CB0} V _{CB} (nA) @ (V) Max	h _{FE} h _{FE} @ (mA) & V _{CE} Min Max	I _C & V _{CE} (mA) (V) 1 1	V _{CE(SAT)} (V) Max	V _{BE(SAT)} V _{BE(ON)} * (V) Min Max		I _C (mA) Max	C _{ob} (pF) Max	f _T (MHz) Min Max	I _C (mA) Max	NF (dB) Max	Test Conditions	Process No.
									I _C (mA) Max	V _{CE} (V) Max							
BC327	TO-92 (97)	50*	45	5	100* 45	40 600 100 1	300 1	0.7	1.2* 1.2*	500 300							67
BC327A	TO-92 (97)	60*	60	5	100* 45	40 400 100 1	300 1	0.7	1.2* 1.2*	300 500							67
BC327-16	TO-92 (97)	50*	45	5	100* 45	40 250 100 1	300 1	0.7	1.2* 1.2*	500 300							67
BC327-25	TO-92 (97)	50*	45	5	100* 45	40 400 100 1	300 1	0.7	1.2* 1.2*	500 300							67
BC328	TO-92 (97)	30*	25	5	100* 25	40 600 100 1	100 1	0.7	1.2 1.2	500 300							67
BC328-25	TO-92 (97)	30*	25	5	100* 25	40 400 100 1	100 1	0.7	1.2 1.2	500 300							67
BC337	TO-92 (97)	50*	45	5	100 20	100 600 100 1	100 1	0.7	0.7	500							12
BC337A	TO-92 (97)	60*	60	5	100 20	100 400 100 1	100 1	0.7	0.7	500							12
BC337-16	TO-92 (97)	50*	45	5	100 20	100 250 100 1	100 1	0.7	0.7	500							12
BC337-25	TO-92 (97)	50*	45	5	100 20	160 400 100 1	100 1	0.7	0.7	500							12
BC338	TO-92 (97)	30*	20	5	100 20	100 600 100 1	100 1	0.7	0.7	500							12
BC368	TO-92 (94)	25*	20	5	10K 25	50 375 500 1A	5 10 1A 1	0.5	0.5	1A			40	10			37 (6-1)

NOTE: National preferred device for each process in bold. Number shown in parentheses indicates location (section-page) of device data sheet.